

# International IR Rectifier

## IRFAG40 1000V, N-CHANNEL

### REPETITIVE AVALANCHE AND $dv/dt$ RATED HEXFET<sup>®</sup> TRANSISTORS THRU-HOLE (TO-204AA/AE)

#### Product Summary

Part Number	BVDSS	RDS(on)	ID
IRFAG40	1000V	3.5Ω	3.9A



The HEXFET<sup>®</sup> technology is the key to International Rectifier's advanced line of power MOSFET transistors. The efficient geometry and unique processing of this latest "State of the Art" design achieves: very low on-state resistance combined with high transconductance; superior reverse energy and diode recovery  $dv/dt$  capability.

The HEXFET transistors also feature all of the well established advantages of MOSFETs such as voltage control, very fast switching, ease of paralleling and temperature stability of the electrical parameters.

They are well suited for applications such as switching power supplies, motor controls, inverters, choppers, audio amplifiers and high energy pulse circuits.

#### Features:

- Repetitive Avalanche Ratings
- Dynamic  $dv/dt$  Rating
- Hermetically Sealed
- Simple Drive Requirements
- Ease of Paralleling

#### Absolute Maximum Ratings

	Parameter		Units
ID @ VGS = 0V, TC = 25°C	Continuous Drain Current	3.9	A
ID @ VGS = 0V, TC = 100°C	Continuous Drain Current	2.5	
IDM	Pulsed Drain Current ①	16	
PD @ TC = 25°C	Max. Power Dissipation	125	W
	Linear Derating Factor	1.0	W/°C
VGS	Gate-to-Source Voltage	±20	V
EAS	Single Pulse Avalanche Energy ②	530	mJ
IAR	Avalanche Current ①	3.9	A
EAR	Repetitive Avalanche Energy ①	12.5	mJ
dv/dt	Peak Diode Recovery $dv/dt$ ③	1.0	V/ns
TJ	Operating Junction	-55 to 150	°C
TSTG	Storage Temperature Range		
	Lead Temperature	300 (0.063 in. (1.6mm) from case for 10s)	
	Weight	11.5(typical)	g

For footnotes refer to the last page

**Electrical Characteristics @ T<sub>j</sub> = 25°C (Unless Otherwise Specified)**

	Parameter	Min	Typ	Max	Units	Test Conditions
BVDSS	Drain-to-Source Breakdown Voltage	1000	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 1.0mA
ΔBVDSS/ΔT <sub>J</sub>	Temperature Coefficient of Breakdown Voltage	—	1.4	—	V/°C	Reference to 25°C, I <sub>D</sub> = 1.0mA
RDS(on)	Static Drain-to-Source On-State Resistance	—	—	3.5	Ω	V <sub>GS</sub> = 10V, I <sub>D</sub> = 2.5A ④
		—	—	4.0		V <sub>GS</sub> = 10V, I <sub>D</sub> = 3.9A ④
VGS(th)	Gate Threshold Voltage	2.0	—	4.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
g <sub>fs</sub>	Forward Transconductance	3.3	—	—	S (Ω)	V <sub>DS</sub> > 15V, I <sub>DS</sub> = 2.5A ④
IDSS	Zero Gate Voltage Drain Current	—	—	25	μA	V <sub>DS</sub> = 800V, V <sub>GS</sub> = 0V
		—	—	250		V <sub>DS</sub> = 800V V <sub>GS</sub> = 0V, T <sub>J</sub> = 125°C
IGSS	Gate-to-Source Leakage Forward	—	—	100	nA	V <sub>GS</sub> = 20V
IGSS	Gate-to-Source Leakage Reverse	—	—	-100		V <sub>GS</sub> = -20V
Q <sub>g</sub>	Total Gate Charge	53	—	120	nC	V <sub>GS</sub> = 10V, I <sub>D</sub> = 3.9A
Q <sub>gs</sub>	Gate-to-Source Charge	5.3	—	12		V <sub>DS</sub> = 500V
Q <sub>gd</sub>	Gate-to-Drain ('Miller') Charge	29	—	66		
t <sub>d(on)</sub>	Turn-On Delay Time	—	—	30	ns	V <sub>DD</sub> = 400V*, I <sub>D</sub> = 3.9A, R <sub>G</sub> = 9.1Ω
t <sub>r</sub>	Rise Time	—	—	50		
t <sub>d(off)</sub>	Turn-Off Delay Time	—	—	170		
t <sub>f</sub>	Fall Time	—	—	50		
L <sub>S</sub> + L <sub>D</sub>	Total Inductance	—	6.1	—	nH	Measured from drain lead (6mm/0.25in. from package) to source lead (6mm/0.25in. from package)
C <sub>iss</sub>	Input Capacitance	—	1700	—	pF	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 25V f = 1.0MHz
C <sub>oss</sub>	Output Capacitance	—	250	—		
C <sub>rss</sub>	Reverse Transfer Capacitance	—	100	—		

\*Equipment Limitation

**Source-Drain Diode Ratings and Characteristics**

	Parameter	Min	Typ	Max	Units	Test Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	3.9	A	
I <sub>SM</sub>	Pulse Source Current (Body Diode) ①	—	—	16		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.8	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 3.9A, V <sub>GS</sub> = 0V ④
t <sub>rr</sub>	Reverse Recovery Time	—	—	1000	nS	T <sub>J</sub> = 25°C, I <sub>F</sub> = 3.9A, di/dt ≤ 100A/μs
QRR	Reverse Recovery Charge	—	—	5.6	μC	V <sub>DD</sub> ≤ 50V ④
t <sub>on</sub>	Forward Turn-On Time	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by L <sub>S</sub> + L <sub>D</sub> .				

**Thermal Resistance**

	Parameter	Min	Typ	Max	Units	Test Conditions
R <sub>thJC</sub>	Junction to Case	—	—	1.0	°C/W	Typical socket mount
R <sub>thJA</sub>	Junction to Ambient	—	—	30		

For footnotes refer to the last page

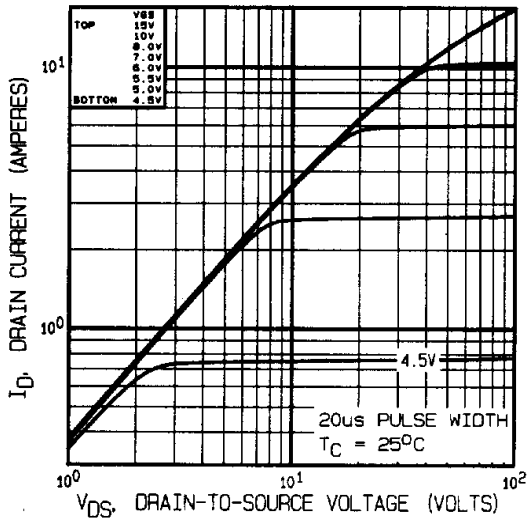


Fig 1. Typical Output Characteristics

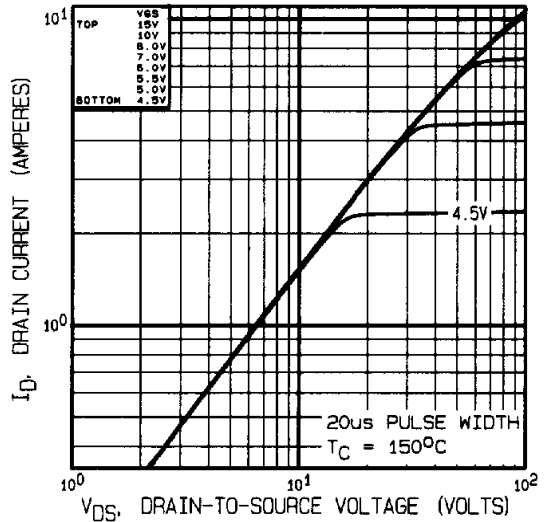


Fig 2. Typical Output Characteristics

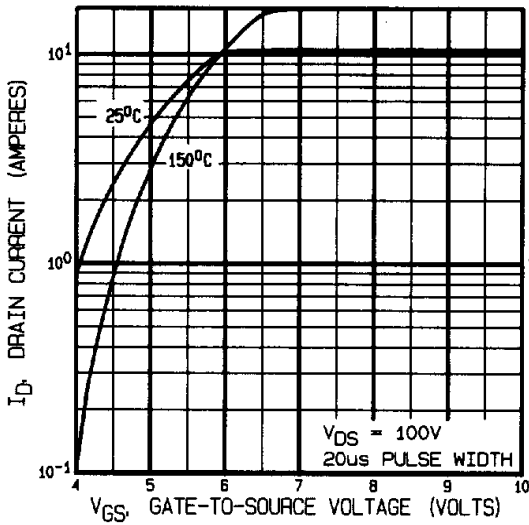


Fig 3. Typical Transfer Characteristics

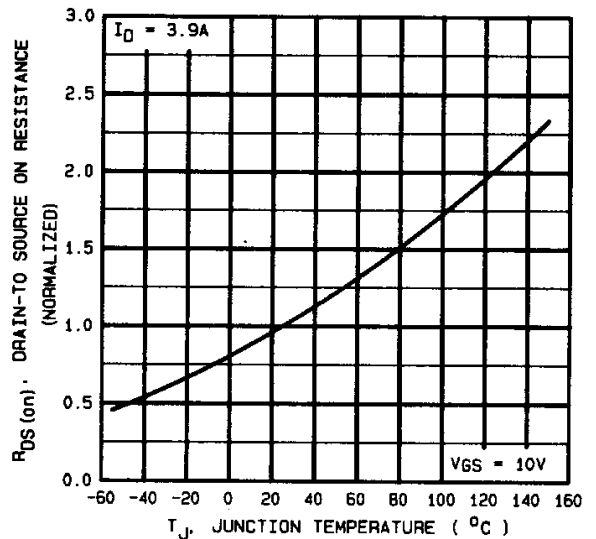


Fig 4. Normalized On-Resistance Vs. Temperature

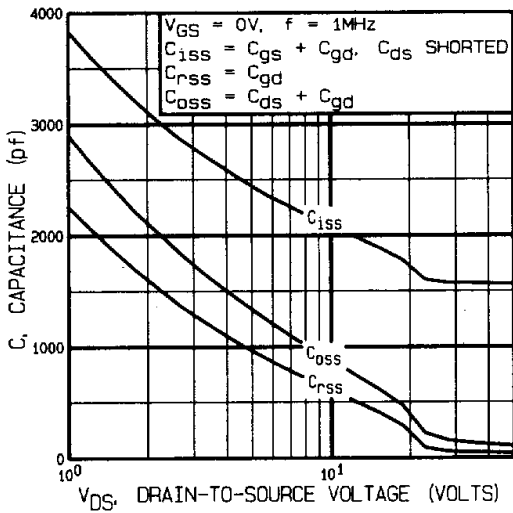


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

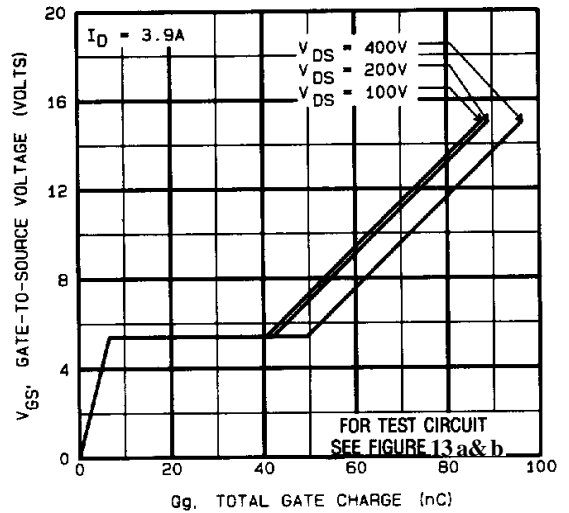


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

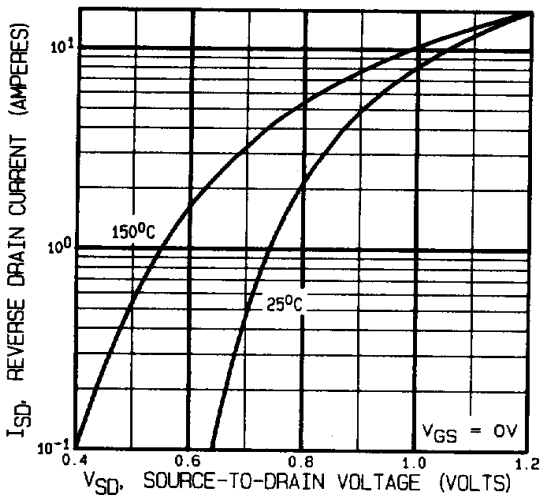


Fig 7. Typical Source-Drain Diode Forward Voltage

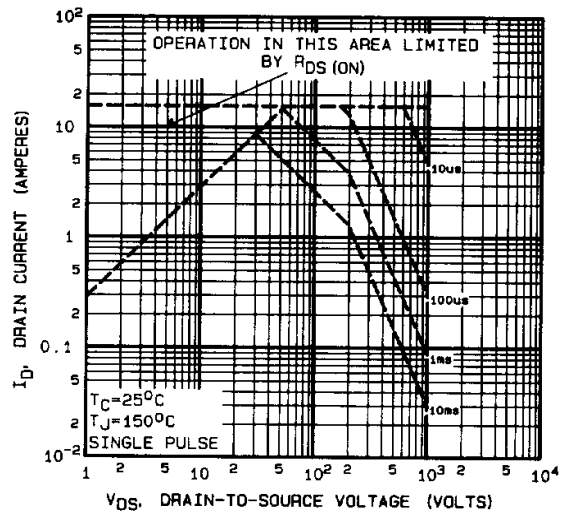


Fig 8. Maximum Safe Operating Area

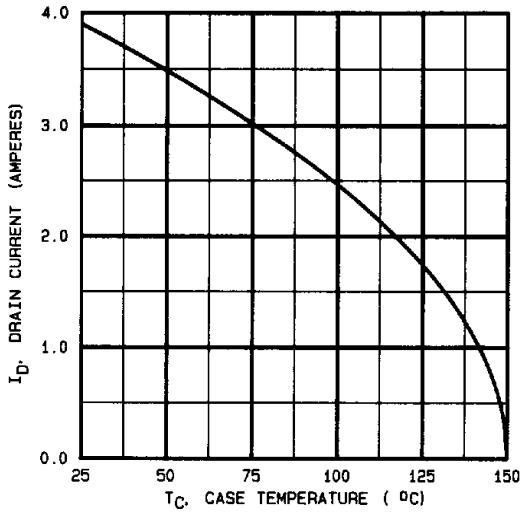


Fig 9. Maximum Drain Current Vs. Case Temperature

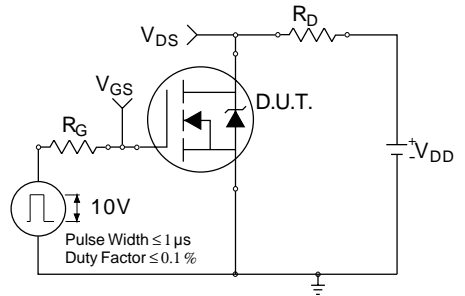


Fig 10a. Switching Time Test Circuit



Fig 10b. Switching Time Waveforms

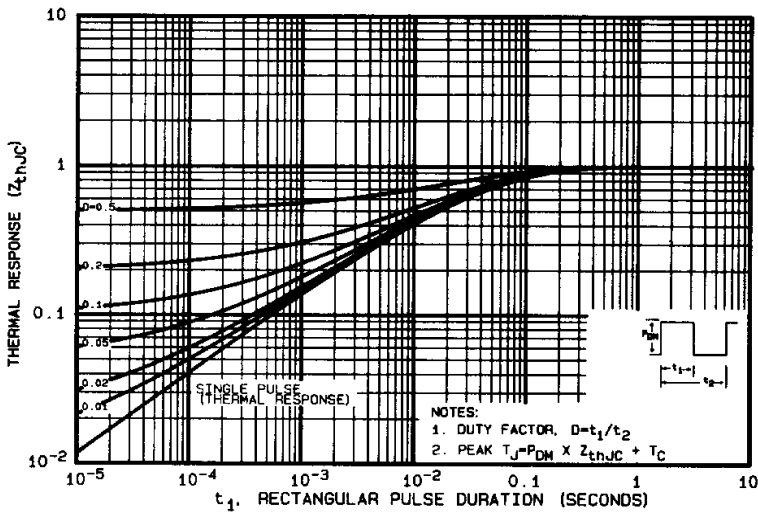


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

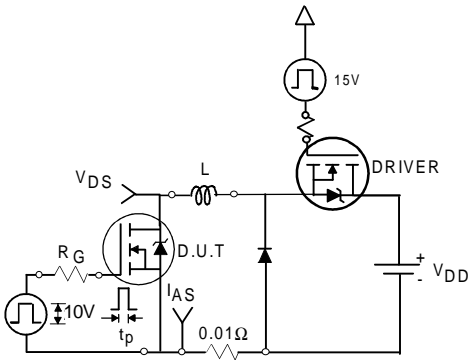


Fig 12a. Unclamped Inductive Test Circuit

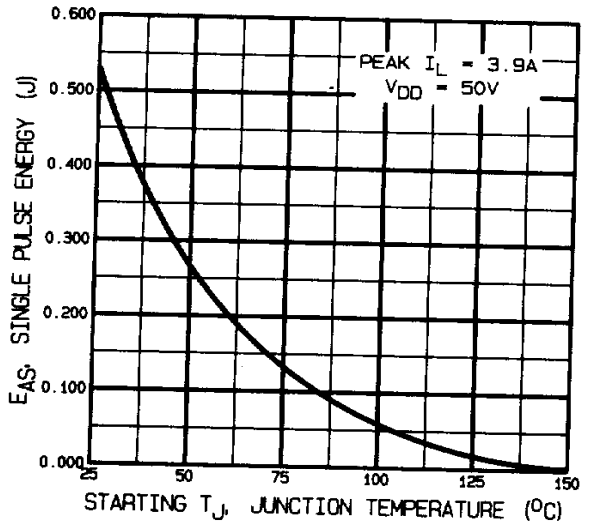


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

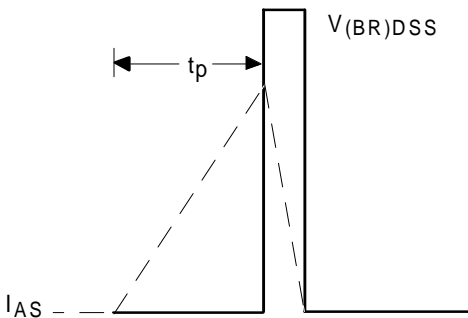


Fig 12b. Unclamped Inductive Waveforms

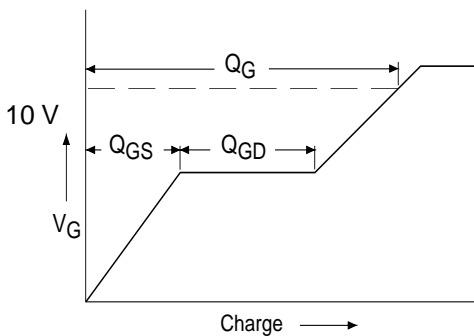


Fig 13a. Basic Gate Charge Waveform

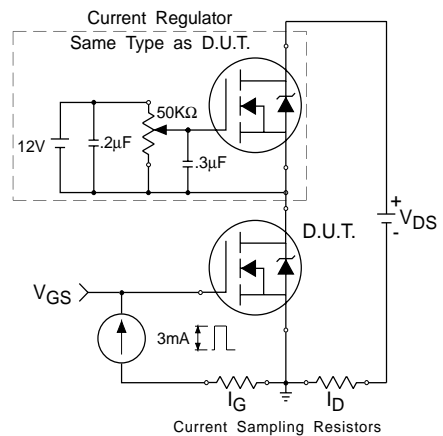
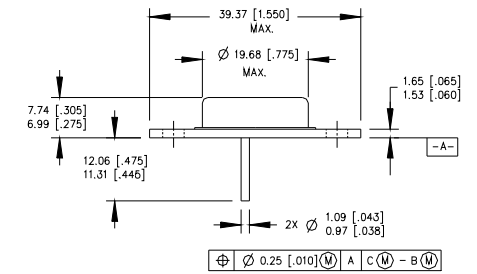


Fig 13b. Gate Charge Test Circuit

**Foot Notes:**

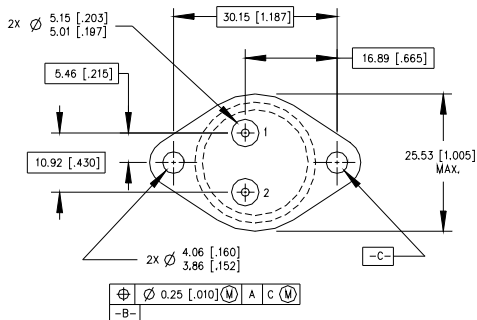
- ① Repetitive Rating; Pulse width limited by maximum junction temperature.
- ②  $V_{DD} = 50V$ , starting  $T_J = 25^{\circ}C$ ,  
Peak  $I_L = 3.9A$ ,
- ③  $I_{SD} \leq 3.9A$ ,  $di/dt \leq 100A/\mu s$ ,  
 $V_{DD} \leq 1000V$ ,  $T_J \leq 150^{\circ}C$   
Suggested  $R_G = 9.1 \Omega$
- ④ Pulse width  $\leq 300 \mu s$ ; Duty Cycle  $\leq 2\%$

**Case Outline and Dimensions —TO-204AA (Modified TO-3)**



PIN ASSIGNMENTS

HEXFET	SCHOTTKY	IGBT
1 - SOURCE	1 - ANODE 1	1 - GATE
2 - GATE	2 - ANODE 2	2 - EMITTER
3 - DRAIN (CASE)	3 - COMMON CATHODE (CASE)	3 - COLLECTOR (CASE)



NOTES:

1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1982.
2. CONTROLLING DIMENSION : INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE TO-204-AA.

**IR WORLD HEADQUARTERS:** 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105  
**IR EUROPEAN REGIONAL CENTRE:** 439/445 Godstone Rd, Whyteleafe, Surrey CR3 OBL, UK Tel: ++ 44 (0)20 8645 8000  
**IR CANADA:** 15 Lincoln Court, Brampton, Ontario L6T3Z2, Tel: (905) 453 2200  
**IR GERMANY:** Saalburgstrasse 157, 61350 Bad Homburg Tel: ++ 49 (0) 6172 96590  
**IR ITALY:** Via Liguria 49, 10071 Borgaro, Torino Tel: ++ 39 011 451 0111  
**IR JAPAN:** K&H Bldg., 2F, 30-4 Nishi-Ikebukuro 3-Chome, Toshima-Ku, Tokyo 171 Tel: 81 (0)3 3983 0086  
**IR SOUTHEAST ASIA:** 1 Kim Seng Promenade, Great World City West Tower, 13-11, Singapore 237994 Tel: ++ 65 (0)838 4630  
**IR TAIWAN:** 16 Fl. Suite D. 207, Sec. 2, Tun Haw South Road, Taipei, 10673 Tel: 886-(0)2 2377 9936  
*Data and specifications subject to change without notice. 1/01*